



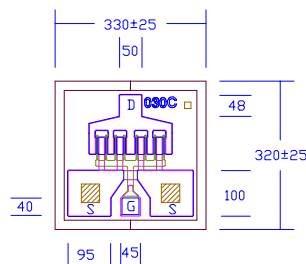
EPA030C/EPA030CV

UPDATED 10/24/2006

High Efficiency Heterojunction Power FET

FEATURES

- +23dBm TYPICAL OUTPUT POWER
- 11dB TYPICAL POWER GAIN FOR EPA030C AND 12.0dB FOR EPA030CV AT 18GHz
- 0.3 X 300 MICRON RECESSED "MUSHROOM" GATE
- Si₃N₄ PASSIVATION AND PLATED HEAT SINK
- ADVANCED EPITAXIAL DOPING PROFILE PROVIDES HIGH POWER EFFICIENCY AND RELIABILITY
- EPA030CV WITH VIA HOLE SOURCE GROUNDING
- Idss SORTED IN 10mA PER BIN RANGE



Chip Thickness: 75 ± 13 microns (EPA030C)
 Chip Thickness: 85 ± 15 microns (EPA030CV)
 ▣ : Via Hole
No Via Hole For EPA030C
 ALL DIMENSIONS IN MICRONS

ELECTRICAL CHARACTERISTICS (T_a = 25°C)



Caution! ESD sensitive device.

SYMBOLS	PARAMETERS/TEST CONDITIONS	EPA030C			EPA030CV			UNIT
		MIN	TYP	MAX	MIN	TYP	MAX	
P_{1dB}	Output Power at 1dB Compression V _{DS} = 8V, I _{DS} ≈ 50% I _{DSS}	21.0	23.0		21.0	23.0		dBm
G_{1dB}	Gain at 1dB Compression V _{DS} = 8V, I _{DS} ≈ 50% I _{DSS}	12.0	13.5		12.5	14.0		dB
PAE	Power Added Efficiency at 1dB Compression V _{DS} = 8V, I _{DS} ≈ 50% I _{DSS}		45			46		%
I_{DSS}	Saturated Drain Current V _{DS} = 3V, V _{GS} = 0V	50	90	130	50	90	130	mA
G_M	Transconductance V _{DS} = 3V, V _{GS} = 0V	60	95		60	95		mS
V_P	Pinch-off Voltage V _{DS} = 3V, I _{DS} = 1.0 mA		-1.0	-2.5		-1.0	-2.5	V
BV_{GD}	Drain Breakdown Voltage I _{GD} = 1.0mA	-13	-15		-13	-15		V
BV_{GS}	Source Breakdown Voltage I _{GS} = 1.0mA	-7	-14		-7	-14		V
R_{th}	Thermal Resistance(Au-Sn Eutectic Attach)		125			95		°C/W

MAXIMUM RATINGS AT 25°C

SYMBOLS	PARAMETERS	EPA030C		EPA030CV	
		ABSOLUTE ¹	CONTINUOUS ²	ABSOLUTE ¹	CONTINUOUS ²
V_{DS}	Drain-Source Voltage	10V	8V	10V	8V
V_{GS}	Gate-Source Voltage	-5V	-3V	-5V	-3V
I_{gf}	Forward Gate Current	1.4mA	0.5mA	1.4mA	0.5mA
I_{gr}	Reverse Gate Current	-0.2mA	-0.1mA	-0.2mA	-0.1mA
P_{in}	Input Power	20dBm	@ 3dB Compression	20dBm	@ 3dB Compression
T_{ch}	Channel Temperature	175°C	175°C	175°C	175°C
T_{stg}	Storage Temperature	-65/175°C	-65/175°C	-65/175°C	-65/175°C
P_t	Total Power Dissipation	1.1W	1.1W	1.5W	1.5W

Note: 1. Exceeding any of the above ratings may result in permanent damage.
 2. Exceeding any of the above ratings may reduce MTTF below design goals.

Specifications are subject to change without notice.

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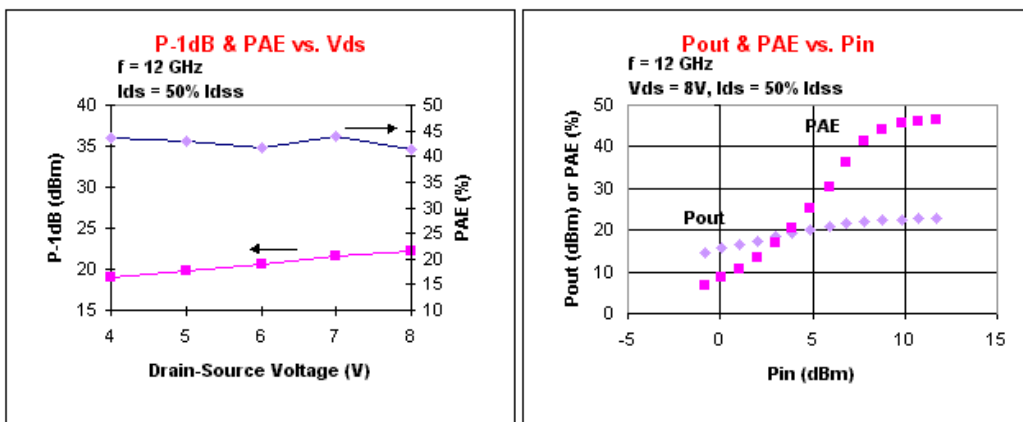
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 Revised October 2006



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S-PARAMETERS

EPA030C 8V, 1/2 Idss

FREQ (GHz)	S11		S21		S12		S22		FREQ (GHz)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG		MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
1.0	0.975	-23.9	7.888	162.4	0.017	76.0	0.750	-9.3	21.0	0.850	130.8	1.761	-0.7	0.069	-18.3	0.404	-121.6
2.0	0.951	-46.7	7.419	147.5	0.032	63.5	0.726	-18.3	22.0	0.854	128.3	1.647	-5.9	0.068	-18.6	0.416	-129.4
4.0	0.883	-85.5	6.169	121.3	0.053	44.0	0.643	-32.0	24.0	0.858	123.8	1.466	-16.0	0.067	-19.4	0.449	-142.5
6.0	0.840	-114.7	4.993	100.9	0.063	30.0	0.577	-41.6	26.0	0.857	120.7	1.336	-25.3	0.067	-16.9	0.489	-153.1
8.0	0.814	-136.9	4.125	84.2	0.067	19.6	0.535	-49.6	28.0	0.860	116.0	1.241	-34.9	0.070	-17.2	0.515	-162.6
10.0	0.801	-154.1	3.495	70.1	0.068	11.2	0.504	-57.1	30.0	0.861	108.2	1.160	-45.6	0.073	-19.5	0.533	-173.0
12.0	0.797	-169.5	3.041	56.7	0.067	4.5	0.479	-65.6	32.0	0.871	98.2	1.071	-56.8	0.072	-23.7	0.552	175.1
14.0	0.791	-175.9	2.700	43.7	0.068	-1.9	0.453	-75.2	34.0	0.895	88.7	0.959	-68.0	0.068	-28.5	0.579	161.5
16.0	0.800	-160.9	2.425	30.4	0.069	-7.5	0.434	-86.1	36.0	0.952	81.3	0.858	-79.0	0.072	-36.4	0.642	146.1
18.0	0.816	-146.4	2.155	17.0	0.070	-12.1	0.411	-98.4	38.0	1.015	74.8	0.765	-91.0	0.073	-51.4	0.702	130.2
20.0	0.832	-133.9	1.913	4.3	0.071	-17.8	0.400	-111.3	40.0	1.002	70.1	0.650	-103.1	0.072	-70.2	0.725	119.1

S-PARAMETERS

EPA030CV 8V, 1/2 Idss

FREQ (GHz)	S11		S21		S12		S22		FREQ (GHz)	S11		S21		S12		S22	
	MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG		MAG	ANG	MAG	ANG	MAG	ANG	MAG	ANG
1.0	0.988	-25.7	7.512	161.8	0.018	75.1	0.778	-9.1	21.0	0.869	130.7	1.524	-5.5	0.069	-26.1	0.425	-115.0
2.0	0.959	-49.8	7.041	146.0	0.034	62.8	0.748	-17.5	22.0	0.875	127.1	1.428	-11.3	0.069	-27.6	0.430	-122.2
4.0	0.888	-91.2	5.765	118.4	0.054	40.8	0.666	-30.0	24.0	0.891	120.3	1.260	-22.6	0.066	-30.9	0.444	-137.9
6.0	0.837	-125.9	4.662	96.0	0.064	25.3	0.599	-38.2	26.0	0.899	114.0	1.103	-33.8	0.063	-34.5	0.470	-153.9
8.0	0.834	-145.7	3.804	80.1	0.067	15.8	0.545	-43.7	28.0	0.905	109.4	0.955	-44.4	0.061	-35.8	0.505	-169.2
10.0	0.829	-162.2	3.181	65.7	0.068	6.8	0.496	-50.1	30.0	0.906	104.4	0.841	-55.7	0.057	-42.1	0.534	175.4
12.0	0.834	-176.4	2.692	50.1	0.068	-2.3	0.466	-58.5	32.0	0.909	100.5	0.735	-66.9	0.054	-50.6	0.569	161.2
14.0	0.847	-162.9	2.305	36.9	0.065	-8.7	0.436	-69.7	34.0	0.929	96.5	0.647	-77.2	0.051	-54.3	0.612	149.5
16.0	0.861	-150.4	1.987	23.9	0.065	-14.2	0.432	-82.3	36.0	0.967	93.1	0.604	-85.6	0.051	-61.8	0.684	140.0
18.0	0.869	-146.0	1.782	12.9	0.068	-18.3	0.418	-98.3	38.0	0.985	88.7	0.559	-96.0	0.063	-75.7	0.726	130.9
20.0	0.867	-136.7	1.590	1.0	0.069	-23.3	0.426	-110.4	40.0	0.986	85.8	0.506	-106.2	0.072	-93.8	0.757	123.9

Note: The data included 0.7 mil diameter Au bonding wires; 1 gate wire, 15 mils each; 1 drain wire, 20 mils each; 4 source wires, 7 mils each; no source wires for EPA030CV.

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Revised October 2006